

**Appl. No. 10/649,076**  
**Amdt. dated March 23, 2005**  
**Reply to Office action of December 23, 2004**

**Amendments to the Specification:**

Please replace paragraph [0027] with the following amended paragraph:

[0001] Figure 5 illustrates the memory element 215 of Figure 3 in greater detail and including read lines 218 and 219. In order to read data from a memory element, read lines 218 and 219 may be electrically coupled to the memory element as illustrated in Figure 5. An inter-layer dielectric (ILD) 220 may electrically isolate write line 216 from read line 218. Likewise, ILD 221 may electrically isolate write line 217 from read line 219. While ILDs 220 and 221 are illustrated separating read and write lines in Figure 53B, subsequent figures may not show an ILD to separate read and write lines for the sake of clarity. It should be understood that an ILD may be included between any read and write conductor pair for electrical isolation. Additionally, although read line 218 and write line 216 are illustrated running in the same direction, this embodiment is not required; and read line 218 and write line 216 may be oriented in any direction with respect to each other. Similarly, read line 219 and write line 217 may also be oriented in any direction with respect to each other. Circuitry (not illustrated in Figure 5) may be electrically coupled to read lines 218 and 219 in order to facilitate reading of memory element 215.